

FIG.1

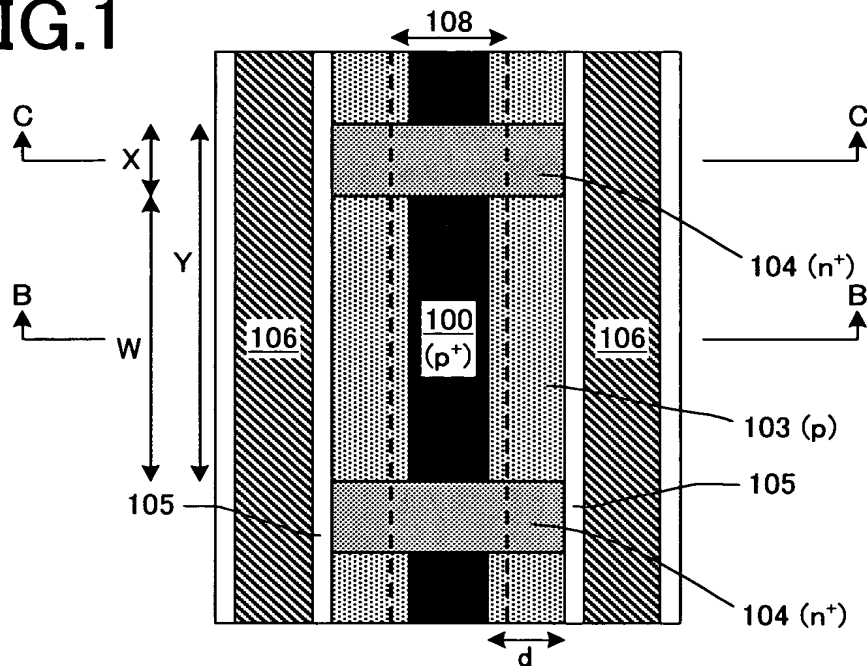


FIG.2

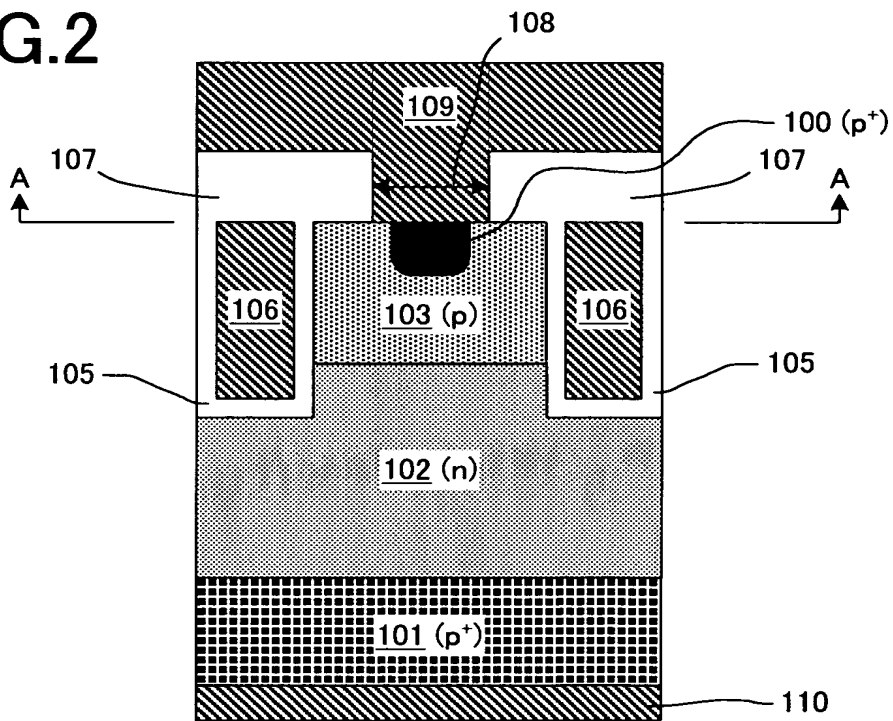


FIG. 3

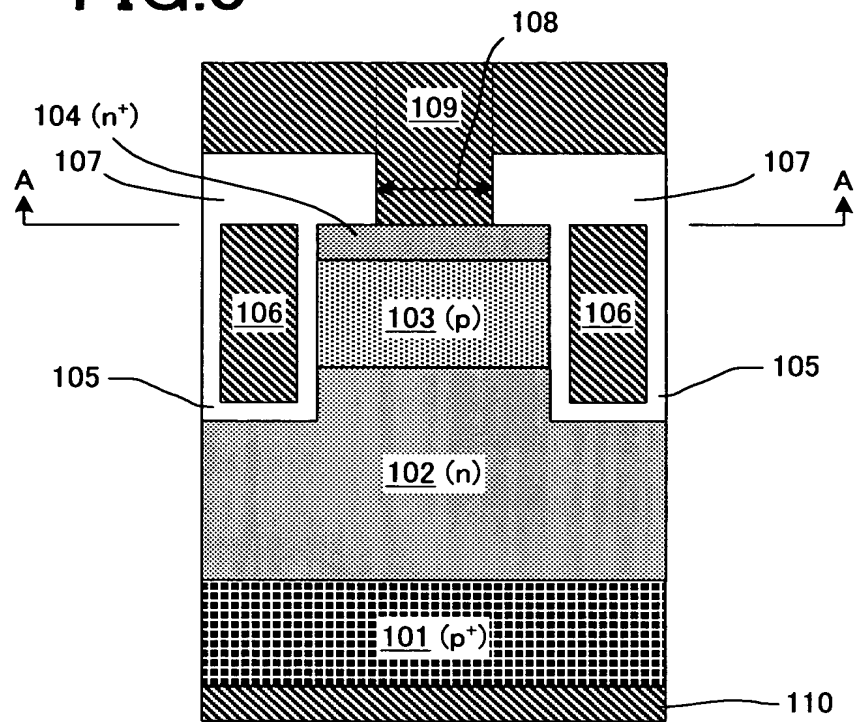


FIG. 4

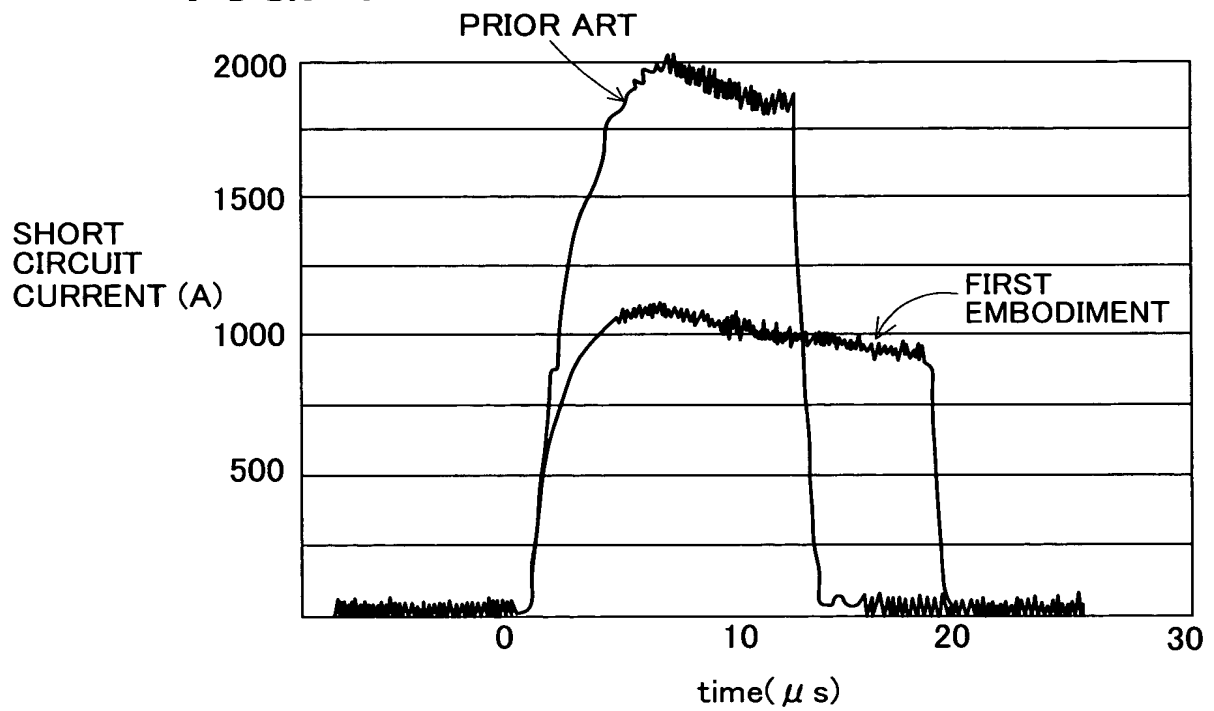


FIG. 5

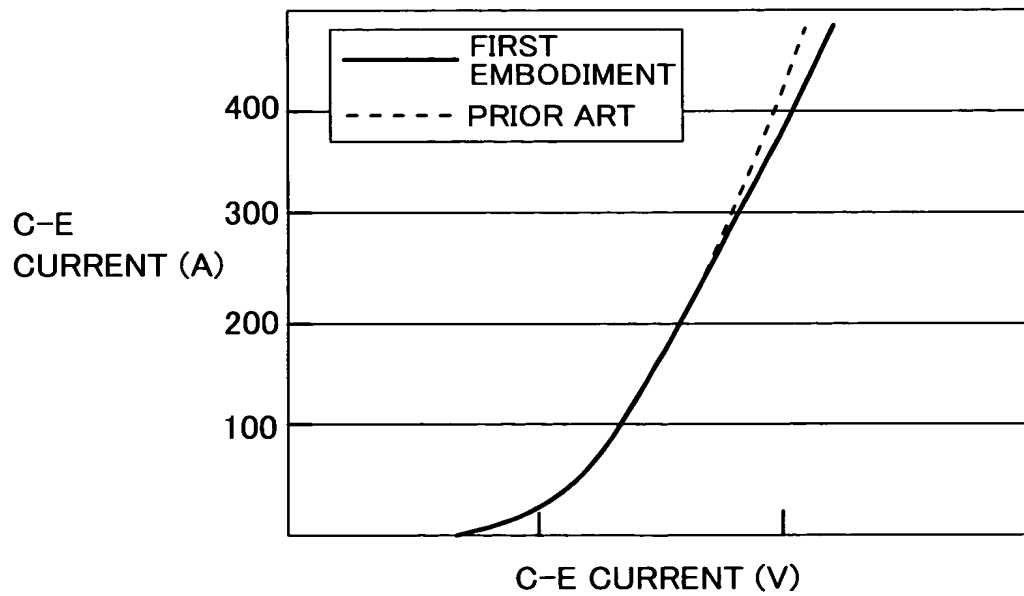


FIG. 6

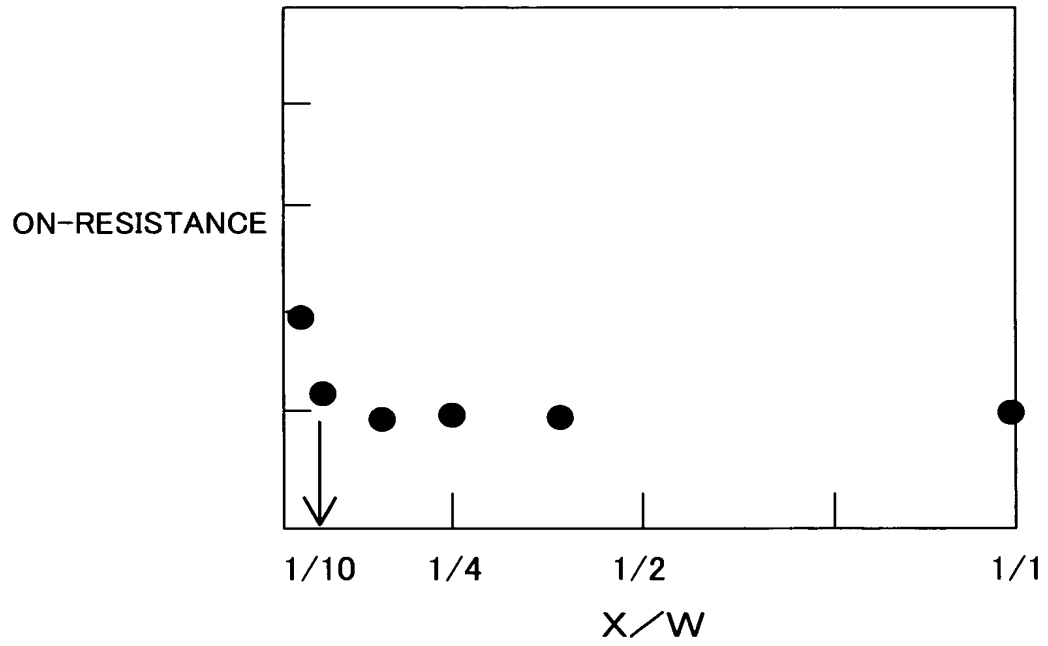


FIG.7

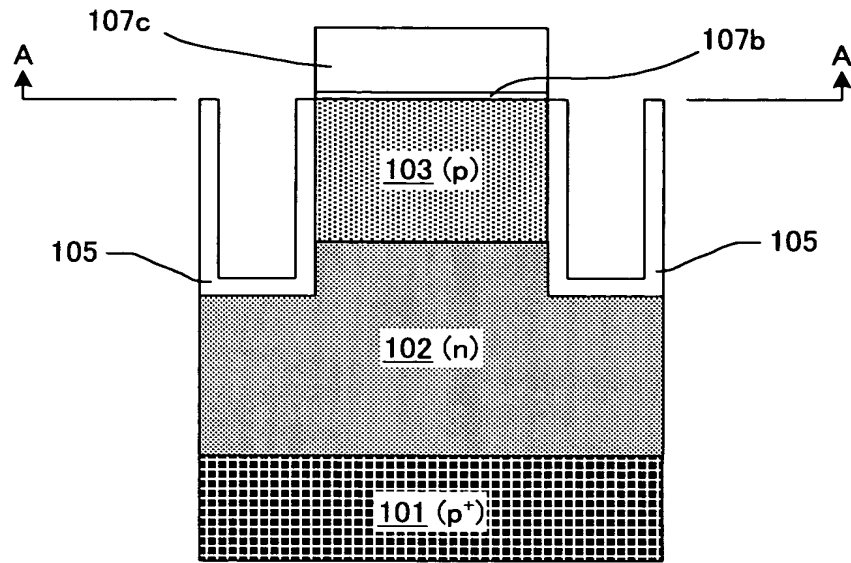


FIG.8

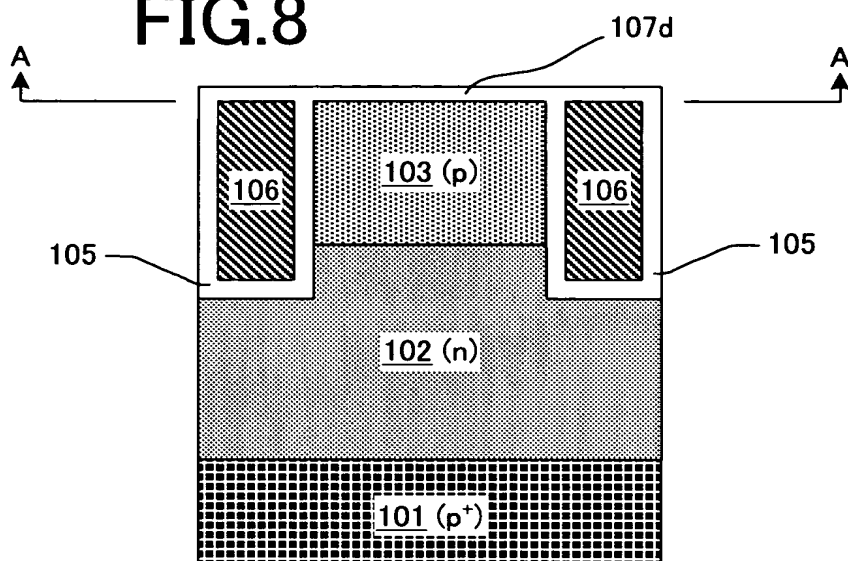


FIG.9

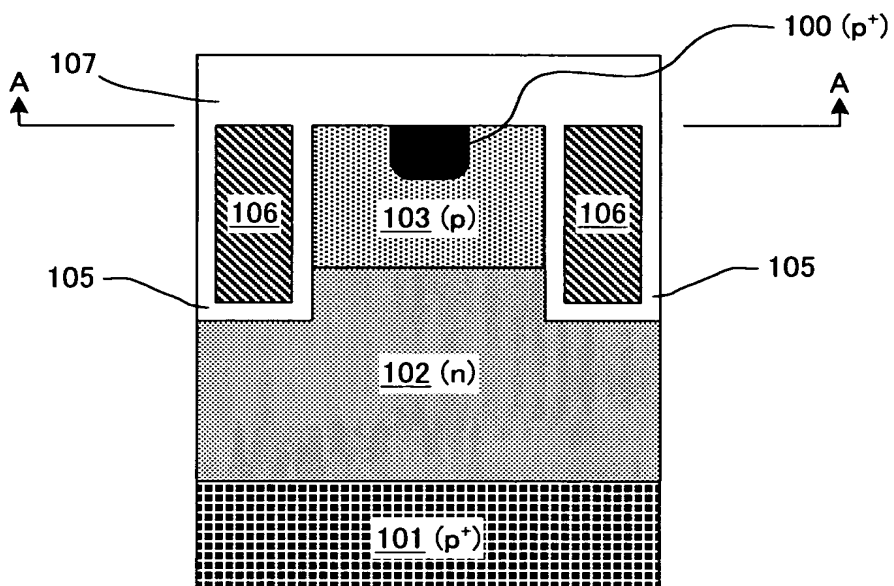


FIG. 10

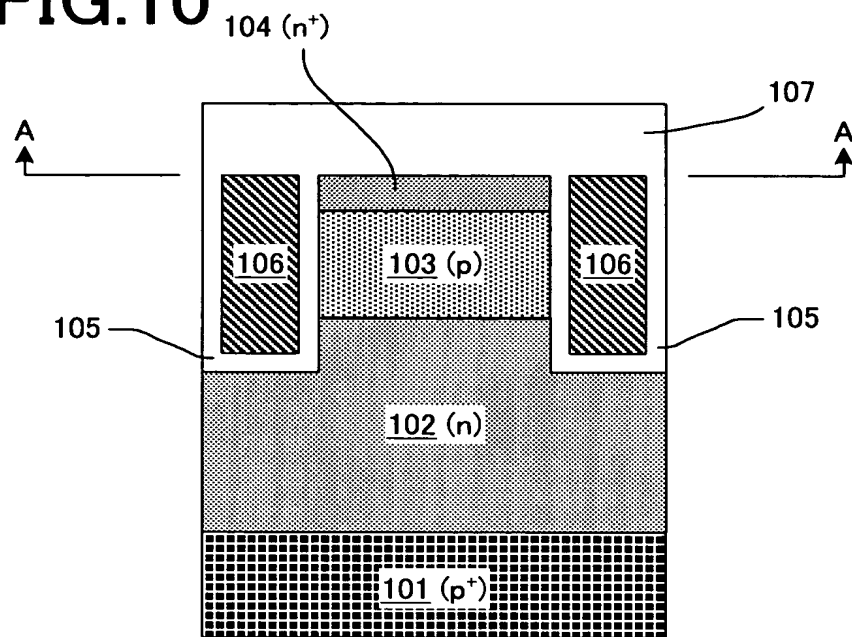
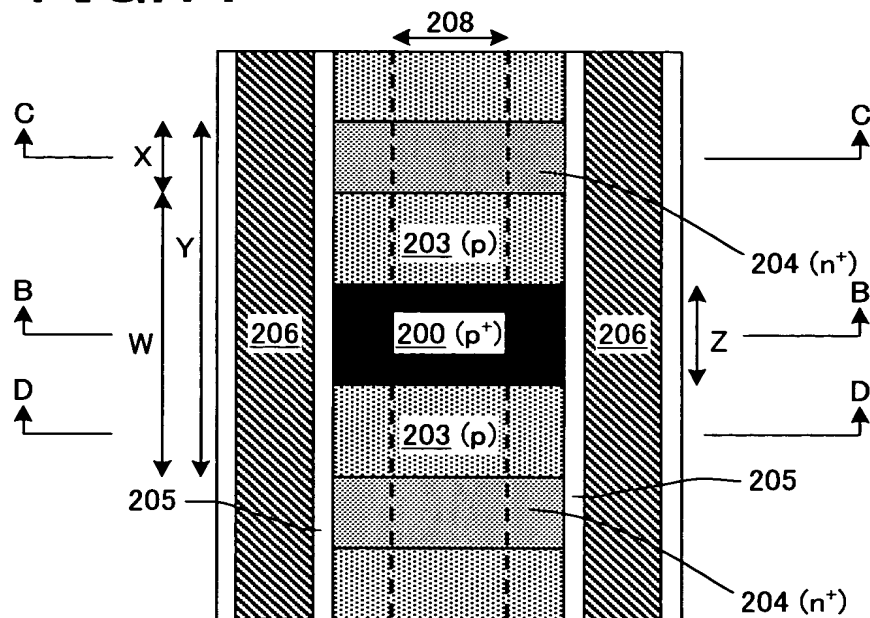
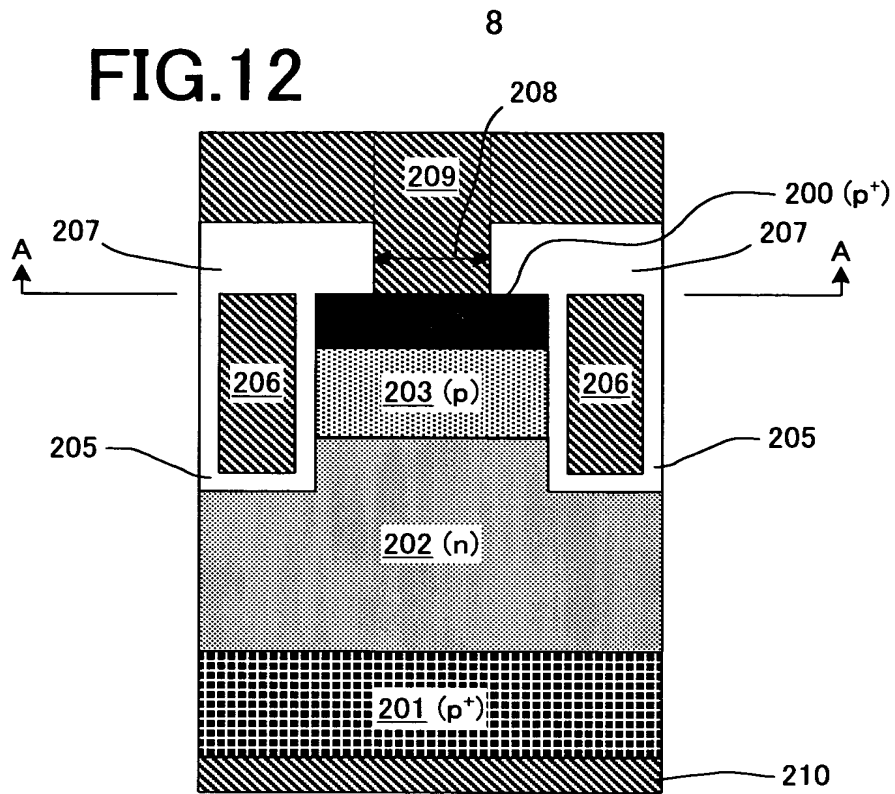


FIG. 11



# FIG.12



# FIG.13

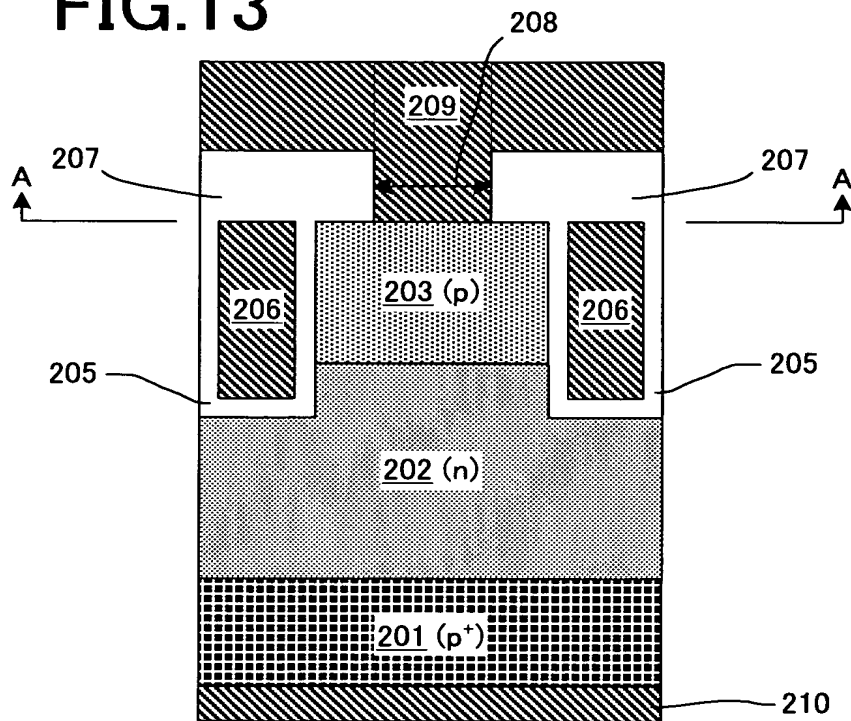




FIG. 14

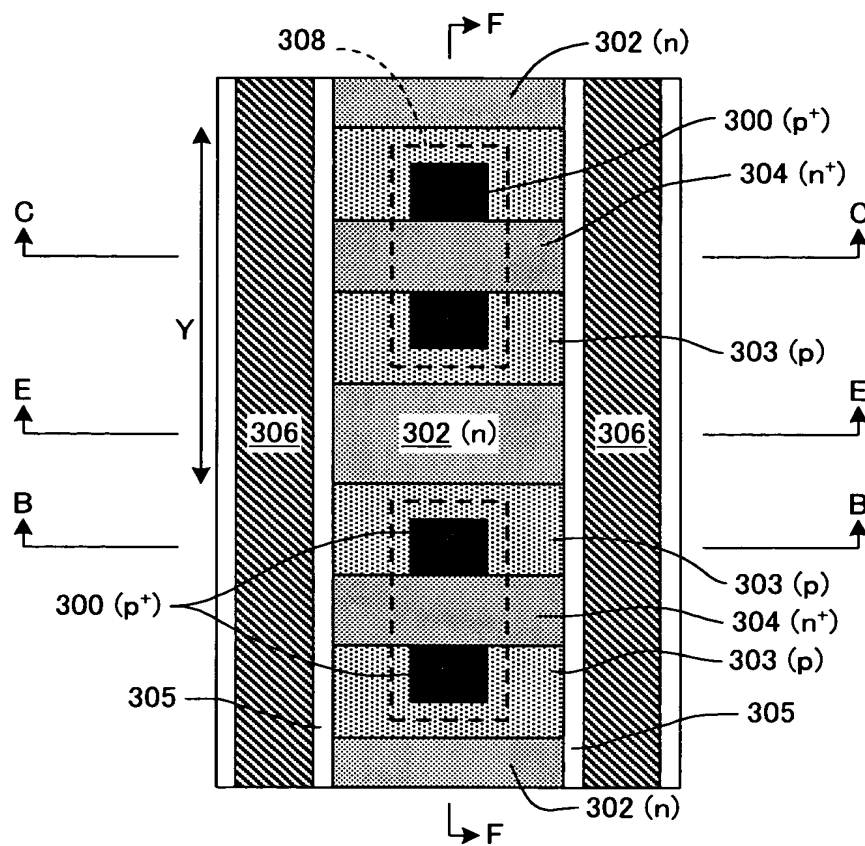


FIG.15

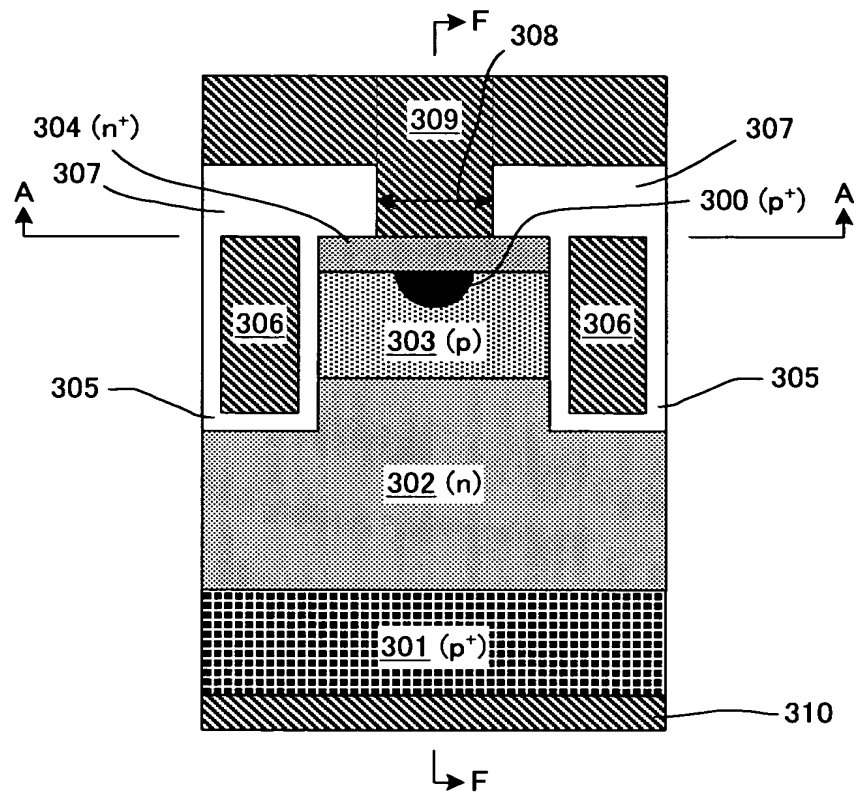


FIG.16

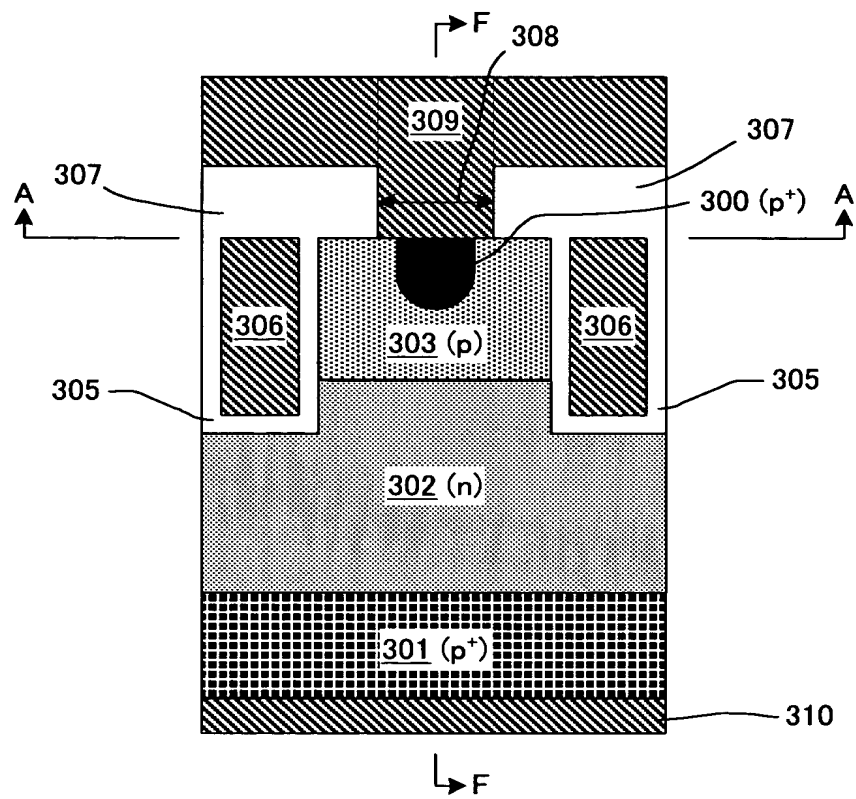


FIG.17

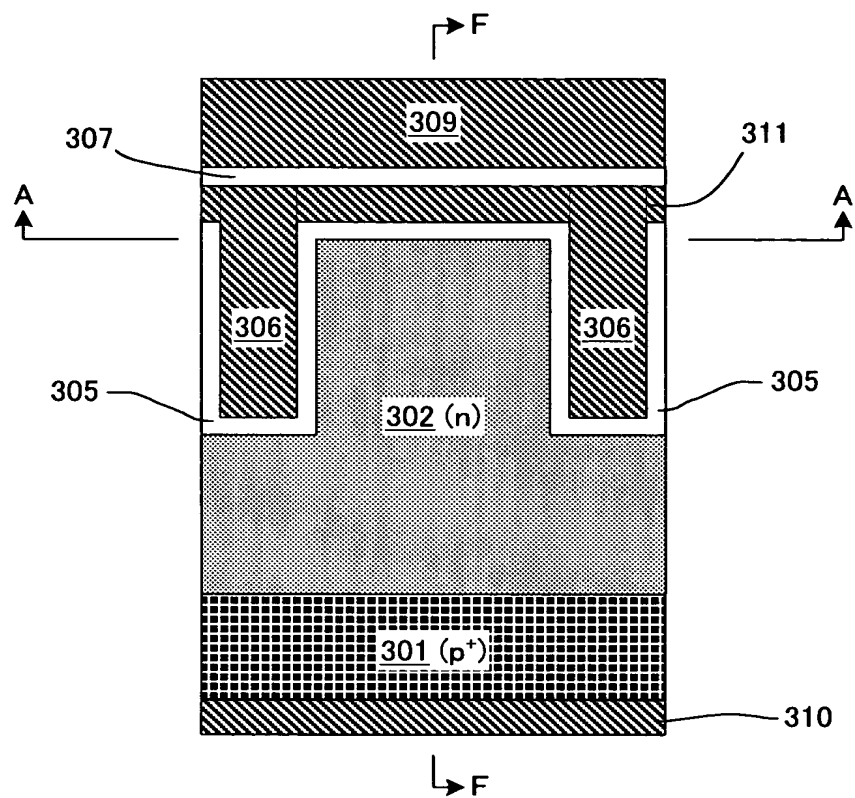


FIG. 18

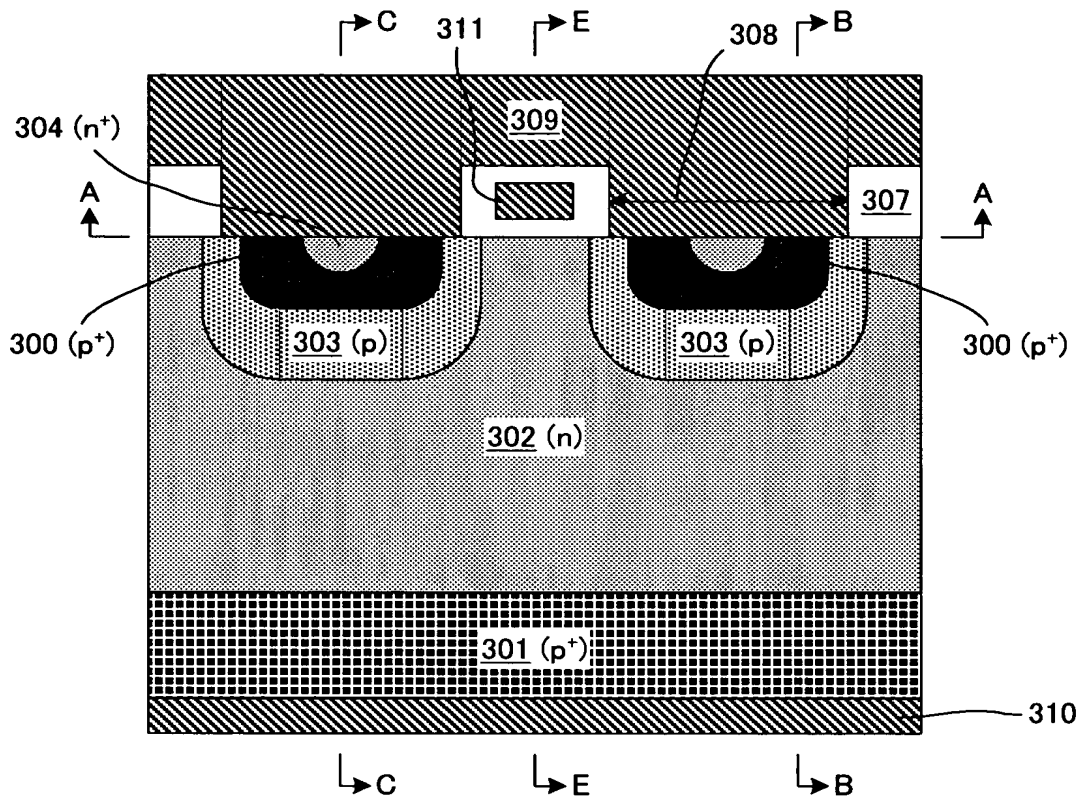


FIG. 19

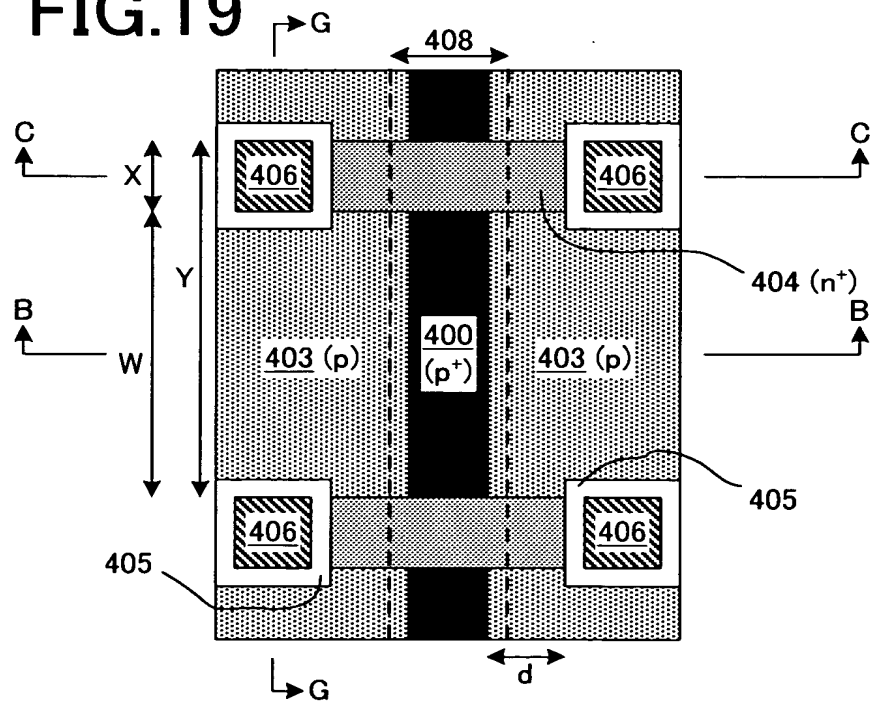


FIG.20

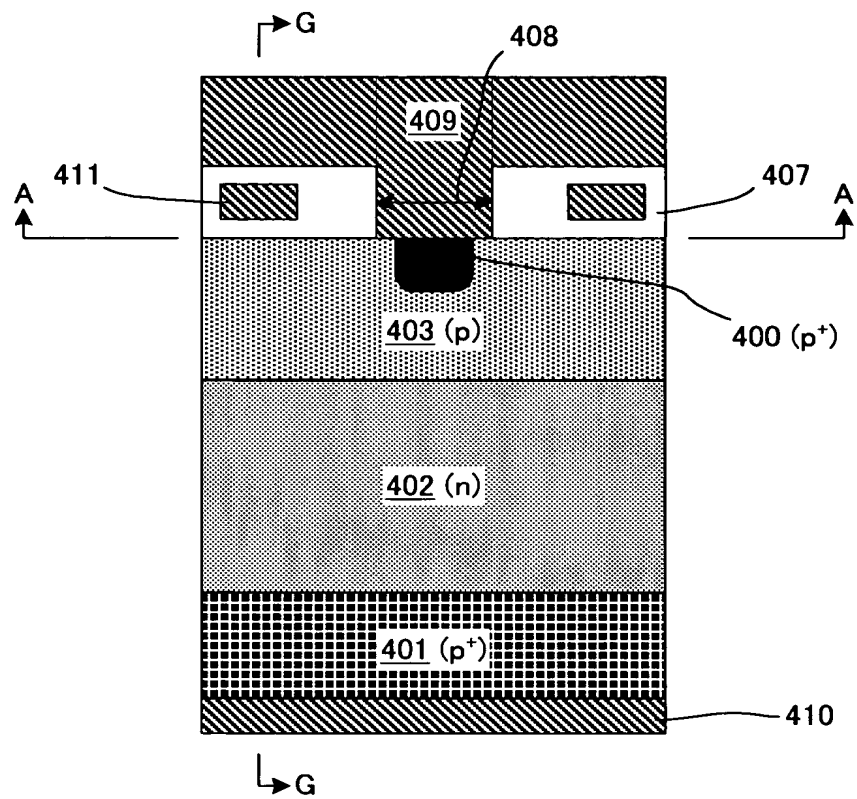


FIG.21

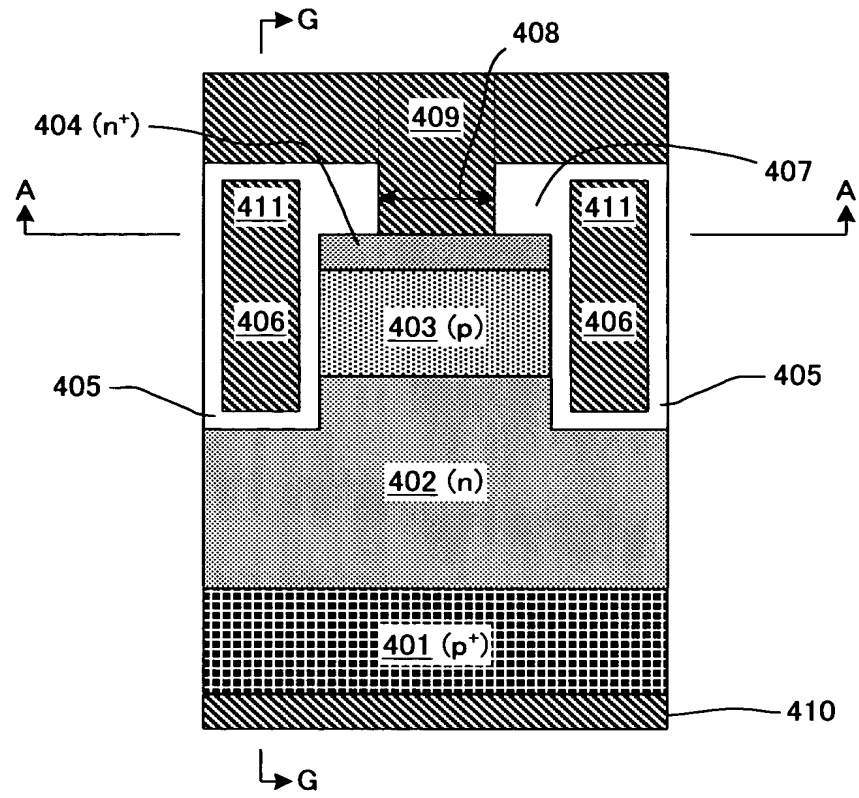


FIG.22

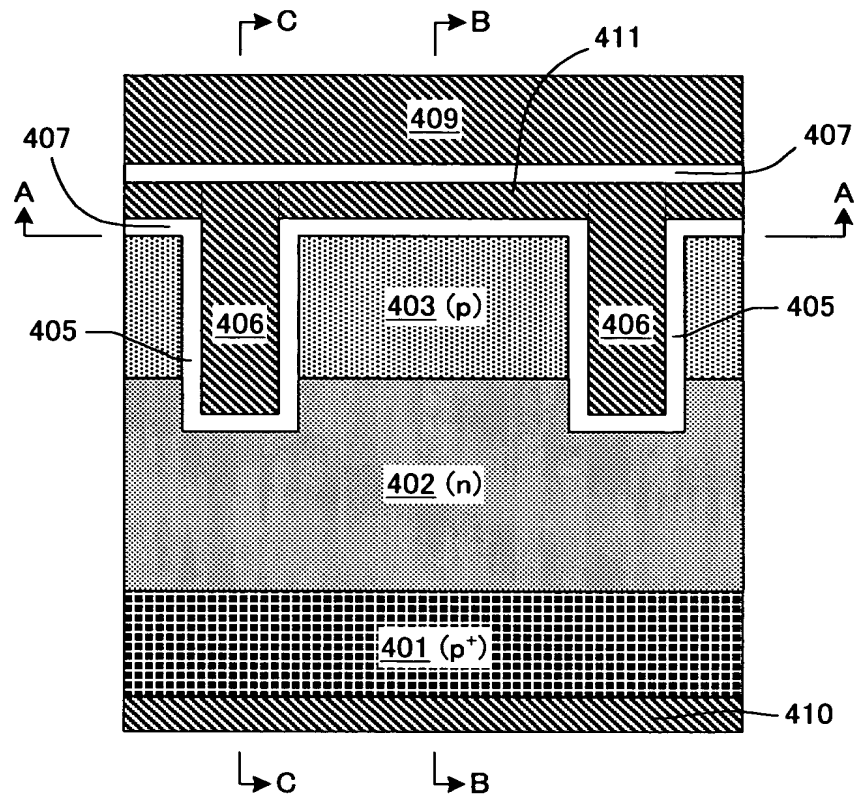




Diagram 500 shows a cross-sectional view of a semiconductor device along the Y-axis. The device consists of alternating layers of n-type semiconductor material 502 and p-type semiconductor material 503. A central region 504 is defined by dashed lines, containing two rectangular regions 506. The device is subjected to forces G and F, and voltages B, E, and C are applied across different layers.

FIG.24

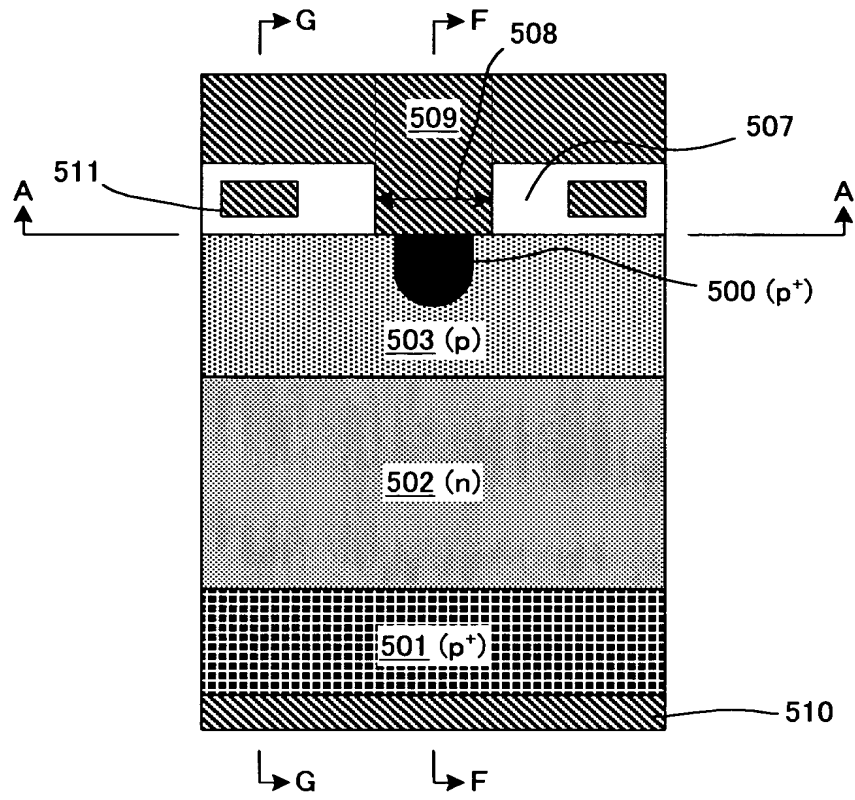


FIG.25

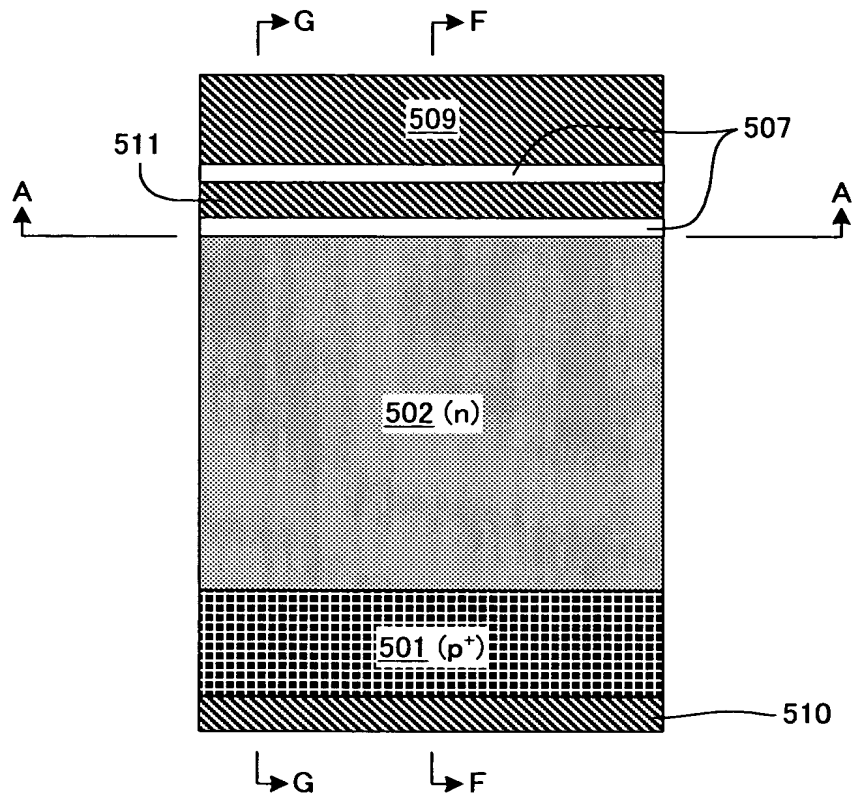
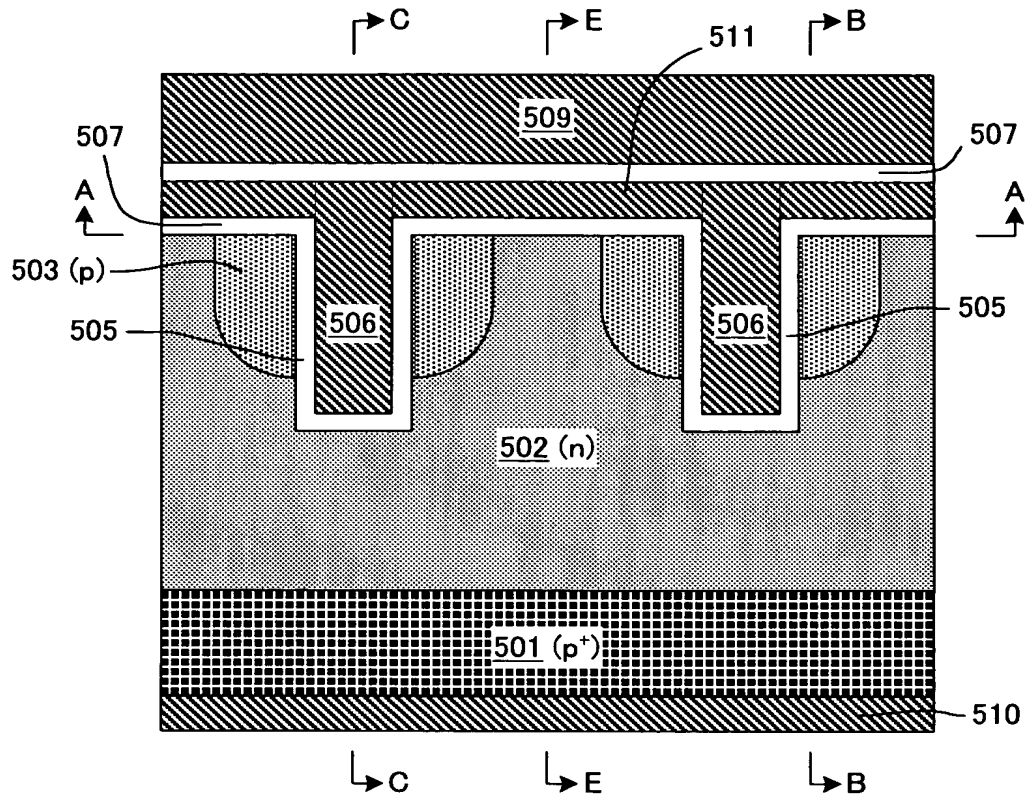


FIG.26



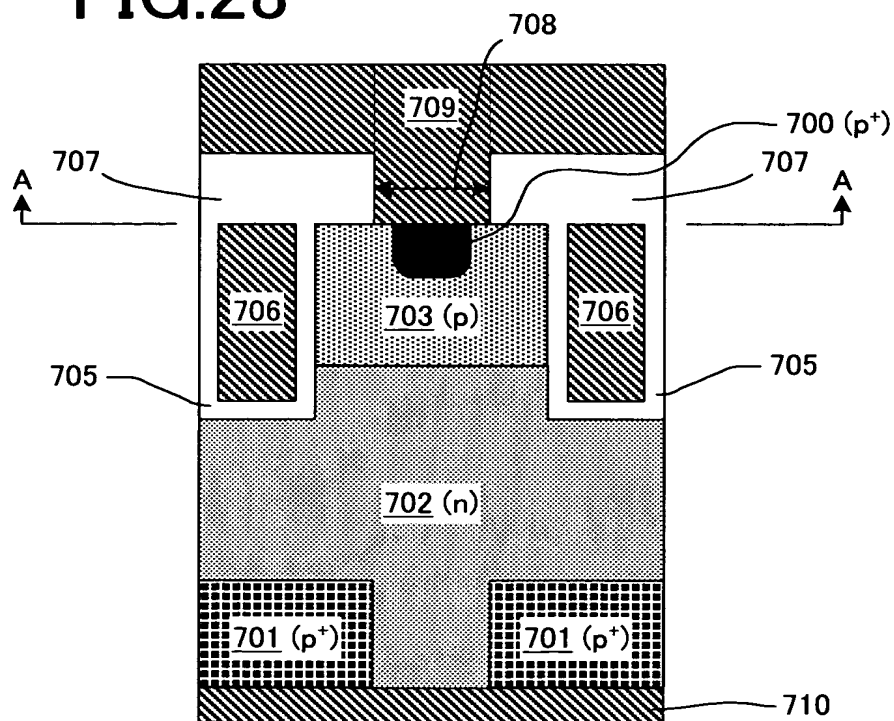


FIG.29

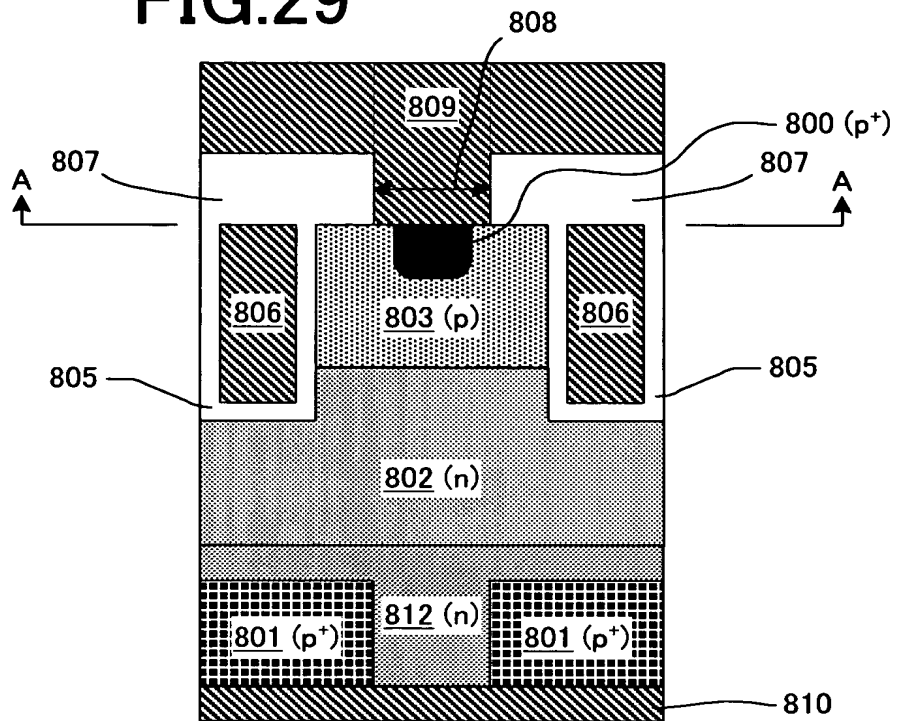
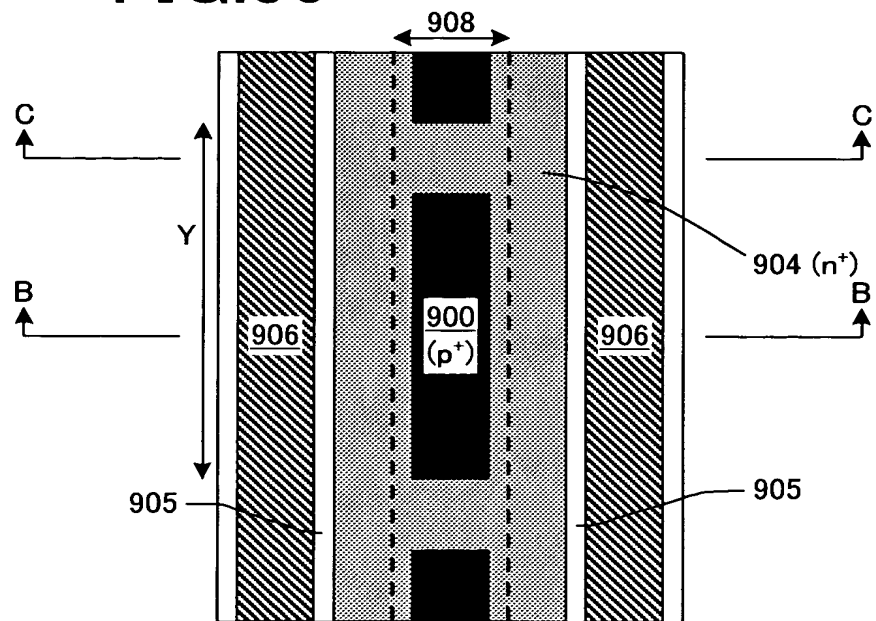


FIG.30



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